NSN 5961-01-170-2170

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

0.570 inches

Terminal Length:

1.000 inches

Overall Diameter:

0.235 inches

Function For Which Designed:

Transient suppressor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-13

Electrode Internally-electrically Connected To Case:

Cathode

Mounting Method:

Terminal

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

171.0 breakdown voltage, dc and 189.0 breakdown voltage, dc

Current Rating Per Characteristic:

200.00 amperes forward current, average preset and 34.00 amperes source cutoff current universal and 5.00 microamperes forward current, average peak

Power Rating Per Characteristic:

1500.0 watts small-signal output power, common-base pascal

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead

Specification Data:

81349-mil-s-19500/500 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0